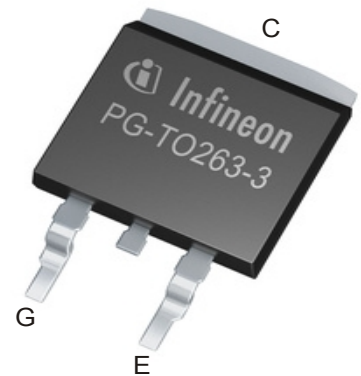


High speed switching series 5th generation

TRENCHSTOP™ 5 high speed soft switching IGBT copacked with full rated current RAPID 1 fast and soft anti parallel diode

Features and Benefits:

- High speed S5 technology offering
- High speed smooth switching device for hard & soft switching
 - Very Low V_{CEsat} , 1.35V at nominal current
 - 650V breakdown voltage
 - Low Q_G
 - IGBT copacked with full rated current RAPID 1 fast antiparallel diode
 - Maximum junction temperature 175°C
 - Pb-free lead plating; RoHS compliant
 - Complete product spectrum and PSpice Models:
<http://www.infineon.com/igbt/>



Potential Applications:

- Energy Generation
 - Solar String Inverter
 - Solar Micro Inverter
- Industrial Power Supplies
 - Industrial SMPS
 - Industrial UPS
- Metal Treatment
 - Welding
- Energy Distribution
 - Energy Storage
- Infrastructure – Charge
 - Charger

Product Validation:

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22



Key Performance and Package Parameters

| Type | V_{CE} | I_C | V_{CEsat} , $T_{vj}=25^{\circ}C$ | T_{vjmax} | Marking | Package |
|-------------|----------|-------|------------------------------------|-------------|---------|------------|
| IKB30N65ES5 | 650V | 30A | 1.35V | 175°C | K30EES5 | PG-TO263-3 |

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High speed switching series 5th generation

Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

| Parameter | Symbol | Value | Unit |
|--|-------------|----------------------|--------------------|
| Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$ | V_{CE} | 650 | V |
| DC collector current, limited by T_{vjmax} $T_c = 25^{\circ}\text{C}$ $T_c = 100^{\circ}\text{C}$ | I_C | 62.0 39.5 | A |
| Pulsed collector current, t_p limited by T_{vjmax} | I_{Cpuls} | 120.0 | A |
| Turn off safe operating area $V_{CE} \leq 650\text{V}$, $T_{vj} \leq 175^{\circ}\text{C}$, $t_p = 1\mu\text{s}$ | - | 120.0 | A |
| Diode forward current, limited by T_{vjmax} $T_c = 25^{\circ}\text{C}$ value limited by bondwire $T_c = 100^{\circ}\text{C}$ | I_F | 40.0 39.5 | A |
| Diode pulsed current, t_p limited by T_{vjmax} | I_{Fpuls} | 120.0 | A |
| Gate-emitter voltage Transient Gate-emitter voltage ($t_p \leq 10\mu\text{s}$, $D < 0.010$) | V_{GE} | ± 20 ± 30 | V |
| Power dissipation $T_c = 25^{\circ}\text{C}$ Power dissipation $T_c = 100^{\circ}\text{C}$ | P_{tot} | 188.0 94.0 | W |
| Operating junction temperature | T_{vj} | -40...+175 | $^{\circ}\text{C}$ |
| Storage temperature | T_{stg} | -55...+150 | $^{\circ}\text{C}$ |
| Soldering temperature, reflow soldering (MSL1 according to JEDEC J-STA-020) | | 260 | $^{\circ}\text{C}$ |

Thermal Resistance

| Parameter | Symbol | Conditions | Value | | | Unit |
|-----------|--------|------------|-------|------|------|------|
| | | | min. | typ. | max. | |

R_{th} Characteristics

| | | | | | | |
|---|---------------|--|---|---|------|-----|
| IGBT thermal resistance, junction - case | $R_{th(j-c)}$ | | - | - | 0.80 | K/W |
| Diode thermal resistance, junction - case | $R_{th(j-c)}$ | | - | - | 1.00 | K/W |
| Thermal resistance, min. footprint junction - ambient | $R_{th(j-a)}$ | | - | - | 65 | K/W |
| Thermal resistance, 6cm ² Cu on PCB junction - ambient | $R_{th(j-a)}$ | | - | - | 40 | K/W |

High speed switching series 5th generation

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | | | Unit |
|--------------------------------------|---------------|--|-------|------|------|---------------|
| | | | min. | typ. | max. | |
| Static Characteristic | | | | | | |
| Collector-emitter breakdown voltage | $V_{(BR)CES}$ | $V_{GE} = 0\text{V}, I_C = 0.20\text{mA}$ | 650 | - | - | V |
| Collector-emitter saturation voltage | V_{CESat} | $V_{GE} = 15.0\text{V}, I_C = 30.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$ | - | 1.35 | 1.70 | V |
| | | | - | 1.50 | - | |
| | | | - | 1.60 | - | |
| Diode forward voltage | V_F | $V_{GE} = 0\text{V}, I_F = 30.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$ | - | 1.45 | 1.70 | V |
| | | | - | 1.42 | - | |
| | | | - | 1.39 | - | |
| Gate-emitter threshold voltage | $V_{GE(th)}$ | $I_C = 0.30\text{mA}, V_{CE} = V_{GE}$ | 3.2 | 4.0 | 4.8 | V |
| Zero gate voltage collector current | I_{CES} | $V_{CE} = 650\text{V}, V_{GE} = 0\text{V}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$ | - | - | 50 | μA |
| | | | - | 1400 | - | |
| Gate-emitter leakage current | I_{GES} | $V_{CE} = 0\text{V}, V_{GE} = 20\text{V}$ | - | - | 100 | nA |
| Transconductance | g_{fs} | $V_{CE} = 20\text{V}, I_C = 30.0\text{A}$ | - | 42.0 | - | S |

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | | | Unit |
|--|-----------|---|-------|------|------|------|
| | | | min. | typ. | max. | |
| Dynamic Characteristic | | | | | | |
| Input capacitance | C_{ies} | $V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$ | - | 1800 | - | pF |
| Output capacitance | C_{oes} | | - | 55 | - | |
| Reverse transfer capacitance | C_{res} | | - | 7 | - | |
| Gate charge | Q_G | $V_{CC} = 520\text{V}, I_C = 30.0\text{A}, V_{GE} = 15\text{V}$ | - | 70.0 | - | nC |
| Internal emitter inductance measured 5mm (0.197 in.) from case | L_E | | - | 7.0 | - | nH |

Switching Characteristic, Inductive Load

| Parameter | Symbol | Conditions | Value | | | Unit |
|-----------|--------|------------|-------|------|------|------|
| | | | min. | typ. | max. | |

IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$

| | | | | | | |
|------------------------|--------------|---|------|------|----|----|
| Turn-on delay time | $t_{d(on)}$ | $T_{vj} = 25^{\circ}\text{C}, V_{CC} = 400\text{V}, I_C = 30.0\text{A}, V_{GE} = 0.0/15.0\text{V}, R_{G(on)} = 13.0\Omega, R_{G(off)} = 13.0\Omega, L_{\sigma} = 30\text{nH}, C_{\sigma} = 30\text{pF}$ L_{σ}, C_{σ} from Fig. E Energy losses include "tail" and diode reverse recovery. | - | 17 | - | ns |
| Rise time | t_r | | - | 12 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 124 | - | ns |
| Fall time | t_f | | - | 30 | - | ns |
| Turn-on energy | E_{on} | | - | 0.56 | - | mJ |
| Turn-off energy | E_{off} | | - | 0.32 | - | mJ |
| Total switching energy | E_{ts} | - | 0.88 | - | mJ | |

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| | | | | | | |
|------------------------|--------------|---|---|------|---|----|
| Turn-on delay time | $t_{d(on)}$ | $T_{vj} = 25^{\circ}C,$ $V_{CC} = 400V, I_C = 15.0A,$ $V_{GE} = 0.0/15.0V,$ $R_{G(on)} = 13.0\Omega, R_{G(off)} = 13.0\Omega,$ $L\sigma = 30nH, C\sigma = 30pF$ $L\sigma, C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery. | - | 16 | - | ns |
| Rise time | t_r | | - | 6 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 133 | - | ns |
| Fall time | t_f | | - | 33 | - | ns |
| Turn-on energy | E_{on} | | - | 0.26 | - | mJ |
| Turn-off energy | E_{off} | | - | 0.17 | - | mJ |
| Total switching energy | E_{ts} | | - | 0.43 | - | mJ |

Diode Characteristic, at $T_{vj} = 25^{\circ}C$

| | | | | | | |
|--|--------------|---|---|------|---|------------|
| Diode reverse recovery time | t_{rr} | $T_{vj} = 25^{\circ}C,$ $V_R = 400V,$ $I_F = 30.0A,$ $di_F/dt = 1200A/\mu s$ | - | 75 | - | ns |
| Diode reverse recovery charge | Q_{rr} | | - | 0.83 | - | μC |
| Diode peak reverse recovery current | I_{rrm} | | - | 18.0 | - | A |
| Diode peak rate of fall of reverse recovery current during t_b | di_{rr}/dt | | - | -900 | - | A/ μs |

| | | | | | | |
|--|--------------|---|---|-------|---|------------|
| Diode reverse recovery time | t_{rr} | $T_{vj} = 25^{\circ}C,$ $V_R = 400V,$ $I_F = 15.0A,$ $di_F/dt = 1900A/\mu s$ | - | 52 | - | ns |
| Diode reverse recovery charge | Q_{rr} | | - | 0.60 | - | μC |
| Diode peak reverse recovery current | I_{rrm} | | - | 18.5 | - | A |
| Diode peak rate of fall of reverse recovery current during t_b | di_{rr}/dt | | - | -1315 | - | A/ μs |

Switching Characteristic, Inductive Load

| Parameter | Symbol | Conditions | Value | | | Unit |
|-----------|--------|------------|-------|------|------|------|
| | | | min. | typ. | max. | |

IGBT Characteristic, at $T_{vj} = 150^{\circ}C$

| | | | | | | |
|------------------------|--------------|--|---|------|---|----|
| Turn-on delay time | $t_{d(on)}$ | $T_{vj} = 150^{\circ}C,$ $V_{CC} = 400V, I_C = 30.0A,$ $V_{GE} = 0.0/15.0V,$ $R_{G(on)} = 13.0\Omega, R_{G(off)} = 13.0\Omega,$ $L\sigma = 30nH, C\sigma = 30pF$ $L\sigma, C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery. | - | 17 | - | ns |
| Rise time | t_r | | - | 13 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 149 | - | ns |
| Fall time | t_f | | - | 55 | - | ns |
| Turn-on energy | E_{on} | | - | 0.77 | - | mJ |
| Turn-off energy | E_{off} | | - | 0.56 | - | mJ |
| Total switching energy | E_{ts} | | - | 1.33 | - | mJ |

| | | | | | | |
|------------------------|--------------|--|---|------|---|----|
| Turn-on delay time | $t_{d(on)}$ | $T_{vj} = 150^{\circ}C,$ $V_{CC} = 400V, I_C = 15.0A,$ $V_{GE} = 0.0/15.0V,$ $R_{G(on)} = 13.0\Omega, R_{G(off)} = 13.0\Omega,$ $L\sigma = 30nH, C\sigma = 30pF$ $L\sigma, C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery. | - | 16 | - | ns |
| Rise time | t_r | | - | 7 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 179 | - | ns |
| Fall time | t_f | | - | 54 | - | ns |
| Turn-on energy | E_{on} | | - | 0.41 | - | mJ |
| Turn-off energy | E_{off} | | - | 0.31 | - | mJ |
| Total switching energy | E_{ts} | | - | 0.72 | - | mJ |

High speed switching series 5th generation

Diode Characteristic, at $T_{vj} = 150^{\circ}\text{C}$

| | | | | | | |
|--|--------------|--|---|-------|---|------------------------|
| Diode reverse recovery time | t_{rr} | $T_{vj} = 150^{\circ}\text{C},$ $V_R = 400\text{V},$ $I_F = 30.0\text{A},$ $di_F/dt = 1200\text{A}/\mu\text{s}$ | - | 110 | - | ns |
| Diode reverse recovery charge | Q_{rr} | | - | 1.75 | - | μC |
| Diode peak reverse recovery current | I_{rrm} | | - | 26.5 | - | A |
| Diode peak rate of fall of reverse recovery current during t_b | di_{rr}/dt | | - | -1000 | - | $\text{A}/\mu\text{s}$ |
| Diode reverse recovery time | t_{rr} | $T_{vj} = 150^{\circ}\text{C},$ $V_R = 400\text{V},$ $I_F = 15.0\text{A},$ $di_F/dt = 1900\text{A}/\mu\text{s}$ | - | 78 | - | ns |
| Diode reverse recovery charge | Q_{rr} | | - | 1.25 | - | μC |
| Diode peak reverse recovery current | I_{rrm} | | - | 26.2 | - | A |
| Diode peak rate of fall of reverse recovery current during t_b | di_{rr}/dt | | - | -1200 | - | $\text{A}/\mu\text{s}$ |

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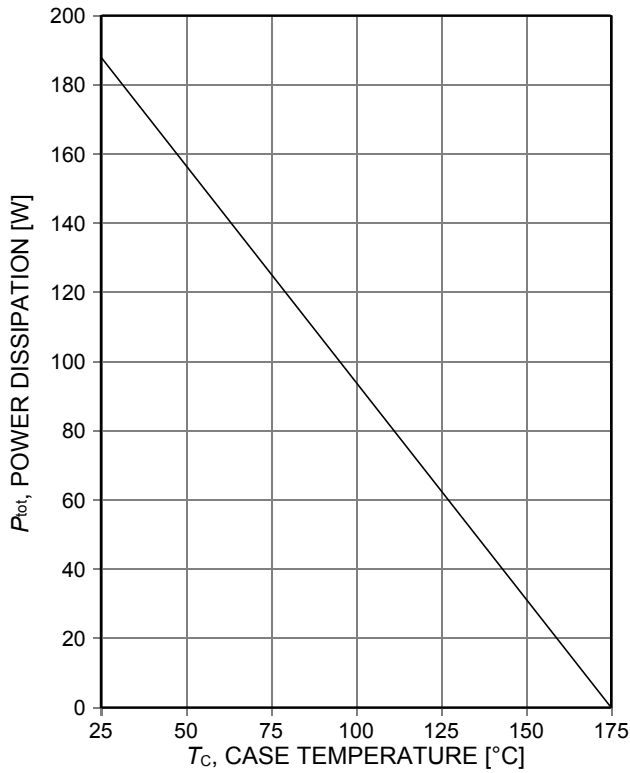


Figure 1. Power dissipation as a function of case temperature ($T_{vj} \leq 175^\circ\text{C}$)

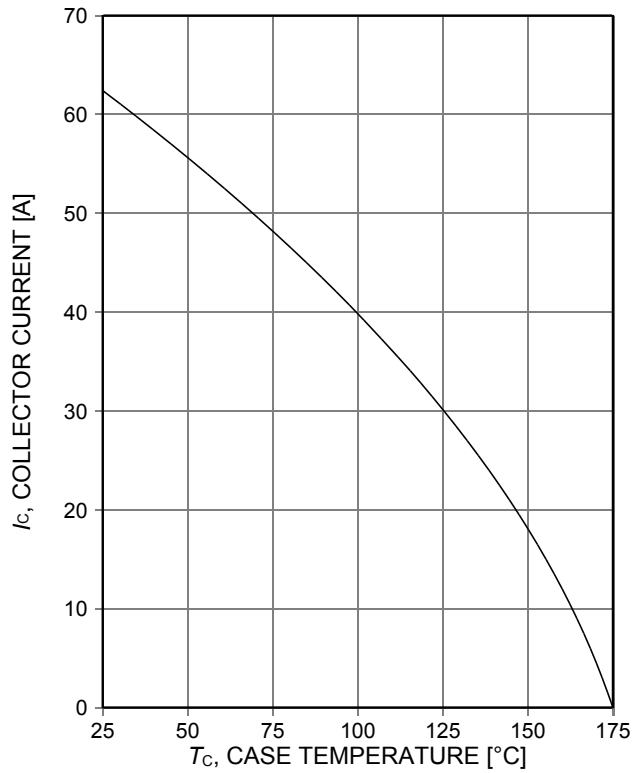


Figure 2. Collector current as a function of case temperature ($V_{GE} \geq 15\text{V}$, $T_{vj} \leq 175^\circ\text{C}$)

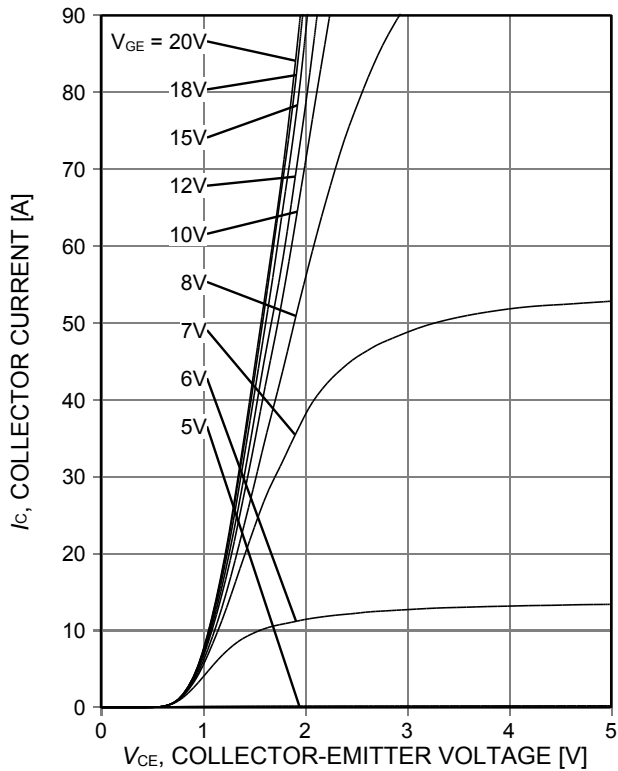


Figure 3. Typical output characteristic ($T_{vj} = 25^\circ\text{C}$)

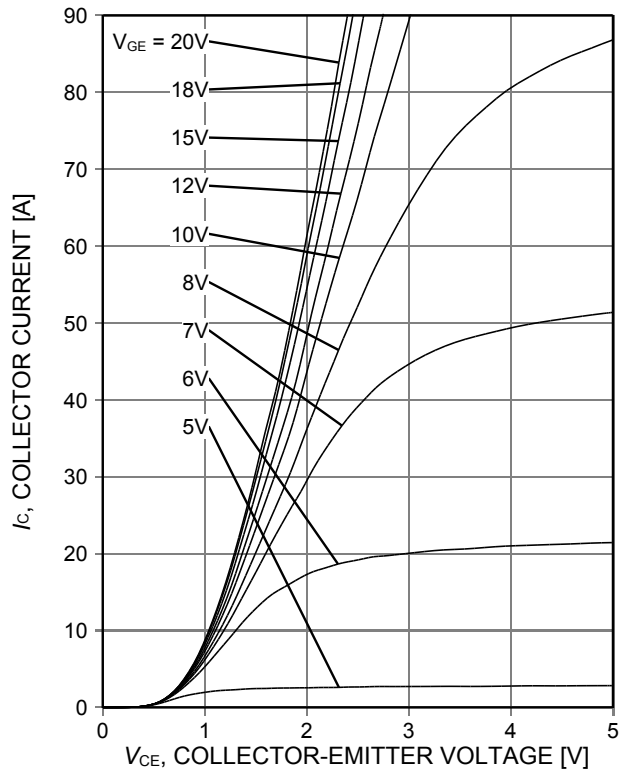


Figure 4. Typical output characteristic ($T_{vj} = 175^\circ\text{C}$)

High speed switching series 5th generation

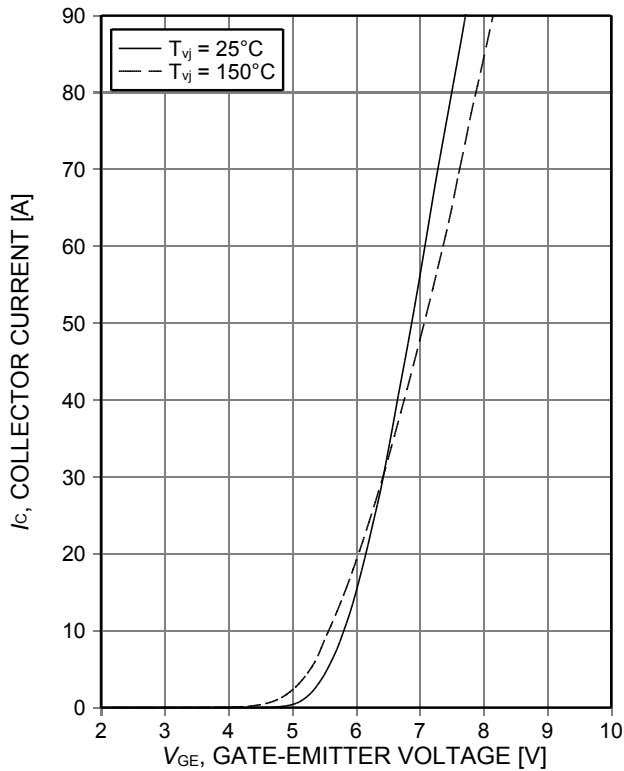


Figure 5. Typical transfer characteristic ($V_{CE}=20\text{V}$)

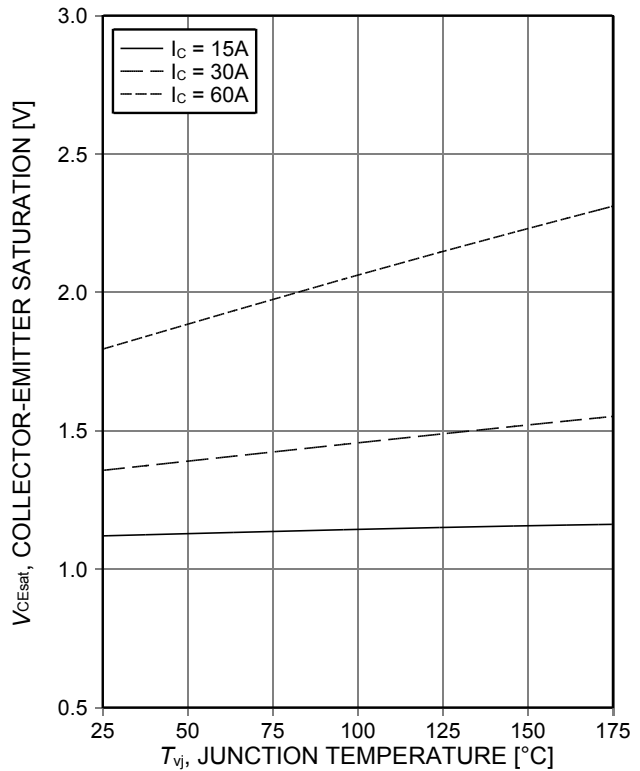


Figure 6. Typical collector-emitter saturation voltage as a function of junction temperature ($V_{GE}=15\text{V}$)

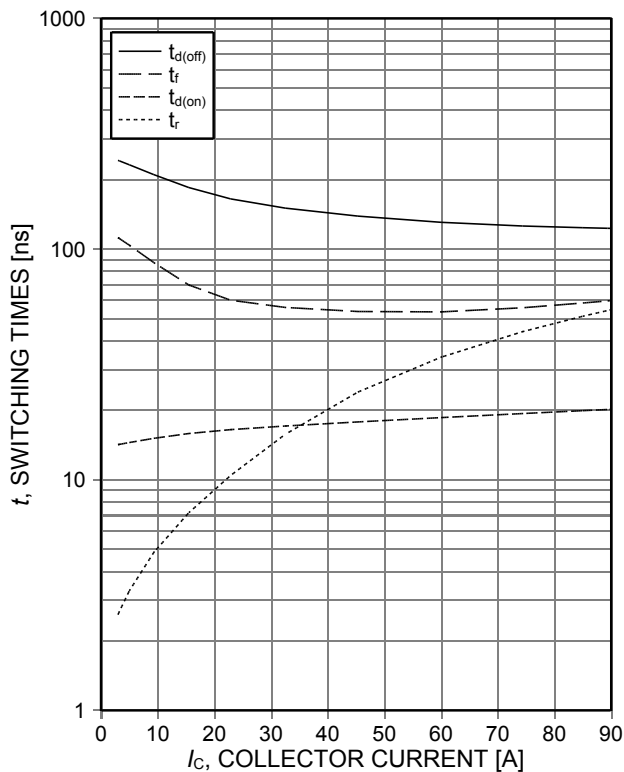


Figure 7. Typical switching times as a function of collector current (inductive load, $T_{vj}=150^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $R_{Gon}=13\Omega$, $R_{Goff}=13\Omega$, dynamic test circuit in Figure E)

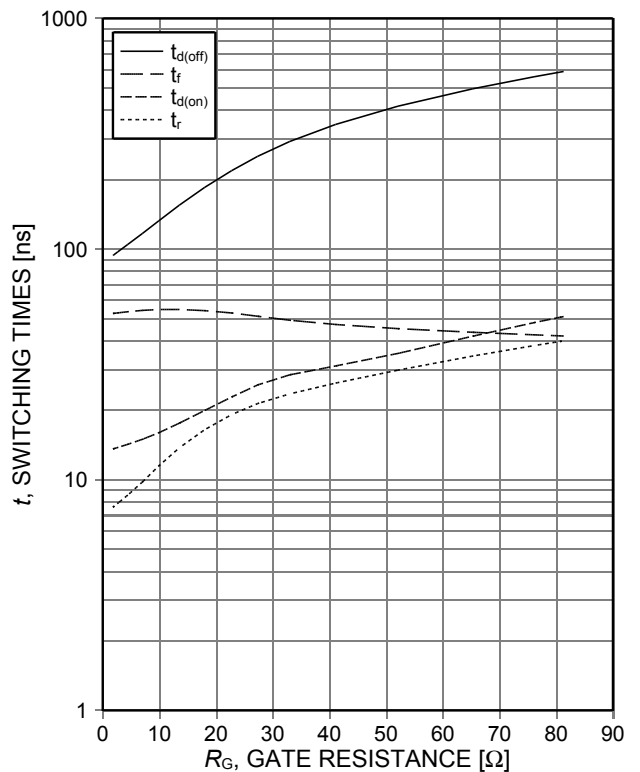


Figure 8. Typical switching times as a function of gate resistance (inductive load, $T_{vj}=150^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $I_c=30\text{A}$, dynamic test circuit in Figure E)

High speed switching series 5th generation

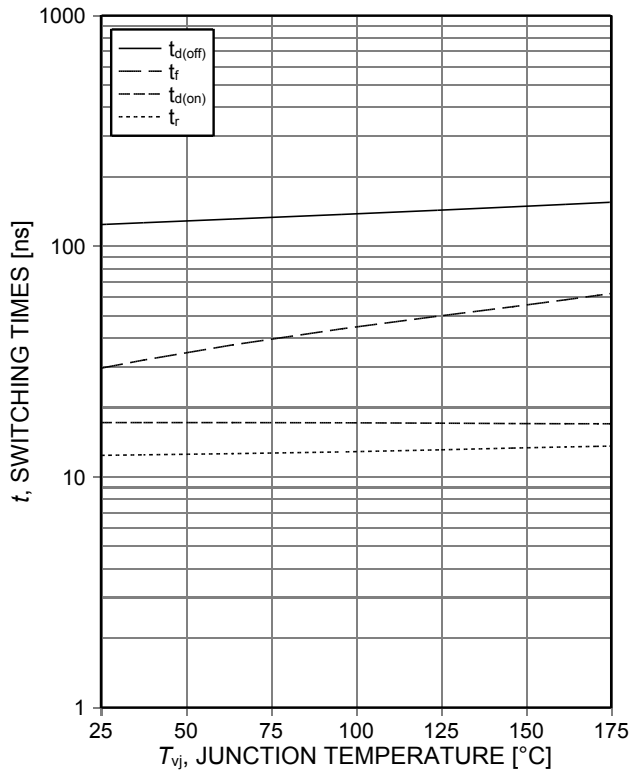


Figure 9. **Typical switching times as a function of junction temperature**
 (inductive load, $V_{CE}=400V$, $V_{GE}=0/15V$, $I_C=30A$, $R_{Gon}=13\Omega$, $R_{Goff}=13\Omega$, dynamic test circuit in Figure E)

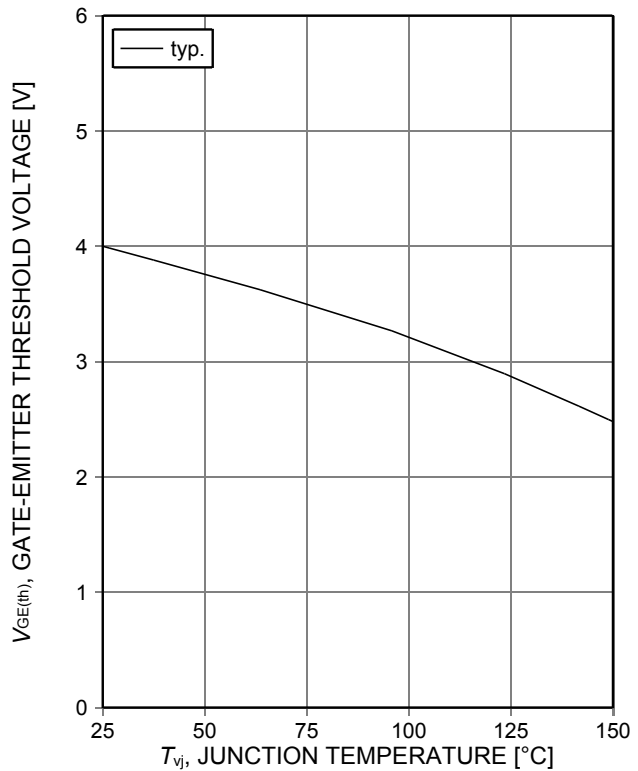


Figure 10. **Gate-emitter threshold voltage as a function of junction temperature**
 ($I_C=0.3mA$)

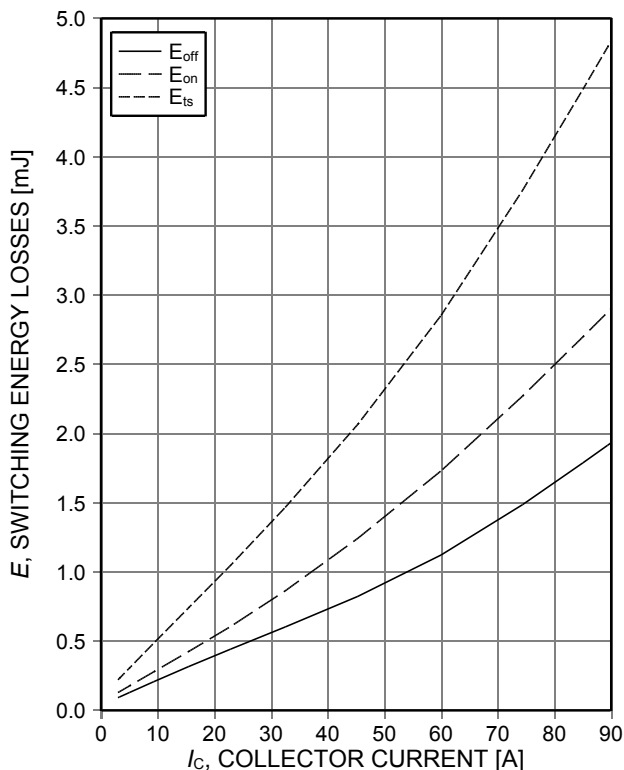


Figure 11. **Typical switching energy losses as a function of collector current**
 (inductive load, $T_{vj}=150^\circ C$, $V_{CE}=400V$, $V_{GE}=150V$, $R_{Gon}=13\Omega$, $R_{Goff}=13\Omega$, dynamic test circuit in Figure E)

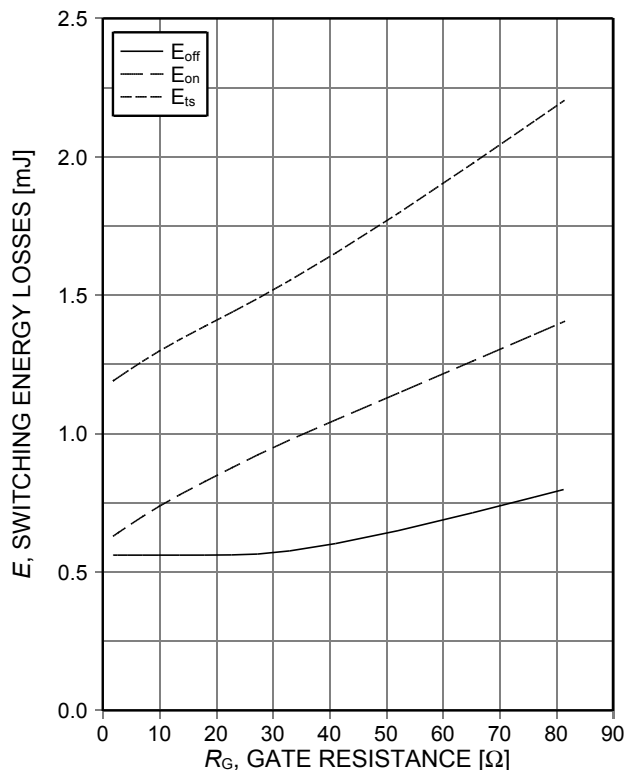


Figure 12. **Typical switching energy losses as a function of gate resistance**
 (inductive load, $T_{vj}=150^\circ C$, $V_{CE}=400V$, $V_{GE}=0/15V$, $I_C=30A$, dynamic test circuit in Figure E)

High speed switching series 5th generation

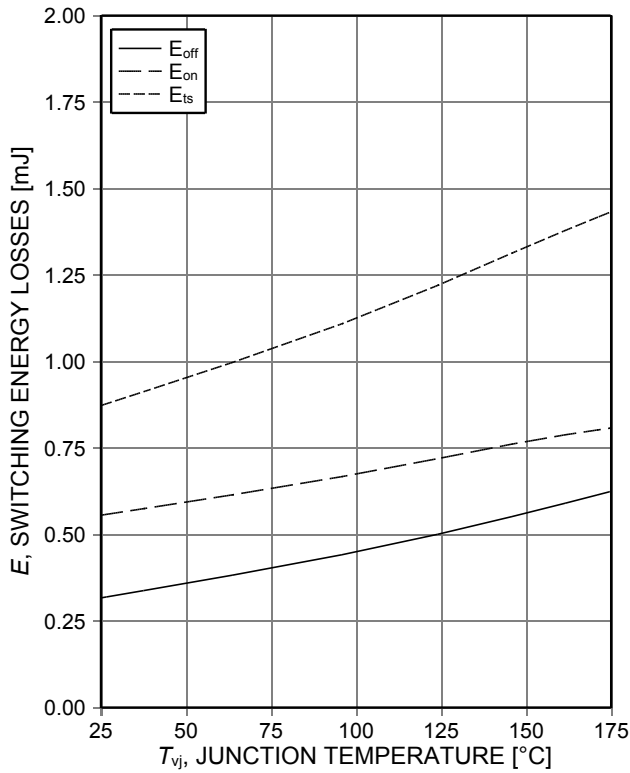


Figure 13. **Typical switching energy losses as a function of junction temperature** (inductive load, $V_{CE}=400V$, $V_{GE}=0/15V$, $I_C=30A$, $R_{Gon}=13\Omega$, $R_{Goff}=13\Omega$, dynamic test circuit in Figure E)

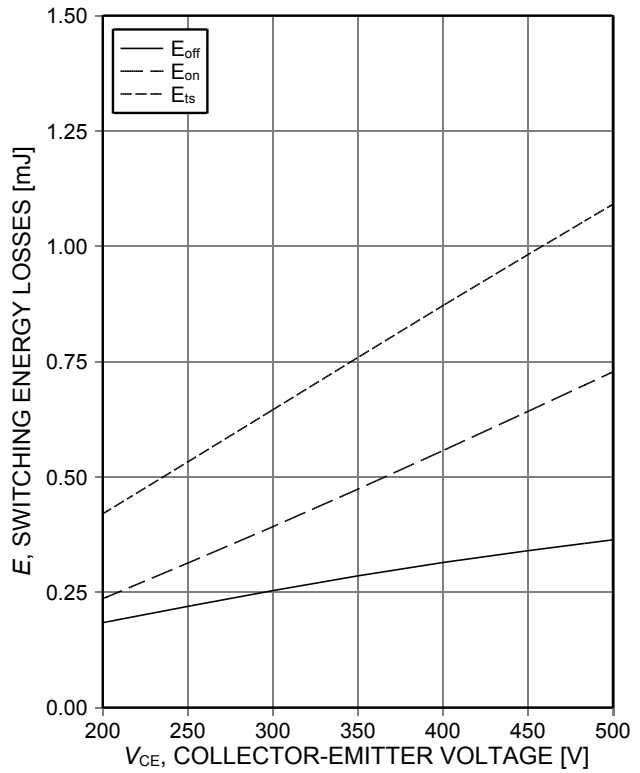


Figure 14. **Typical switching energy losses as a function of collector emitter voltage** (inductive load, $T_{vj}=150^\circ C$, $V_{GE}=0/15V$, $I_C=30A$, $R_{Gon}=13\Omega$, $R_{Goff}=13\Omega$, dynamic test circuit in Figure E)

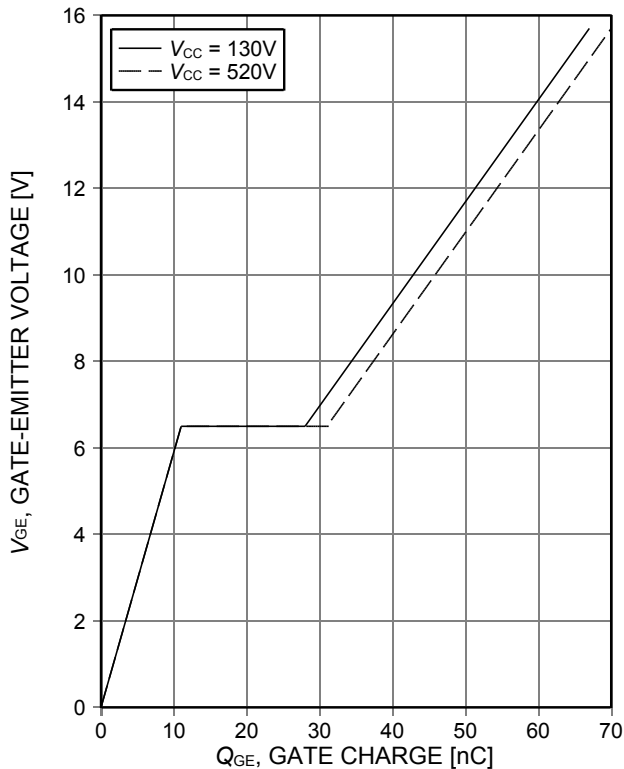


Figure 15. **Typical gate charge** ($I_C=30A$)

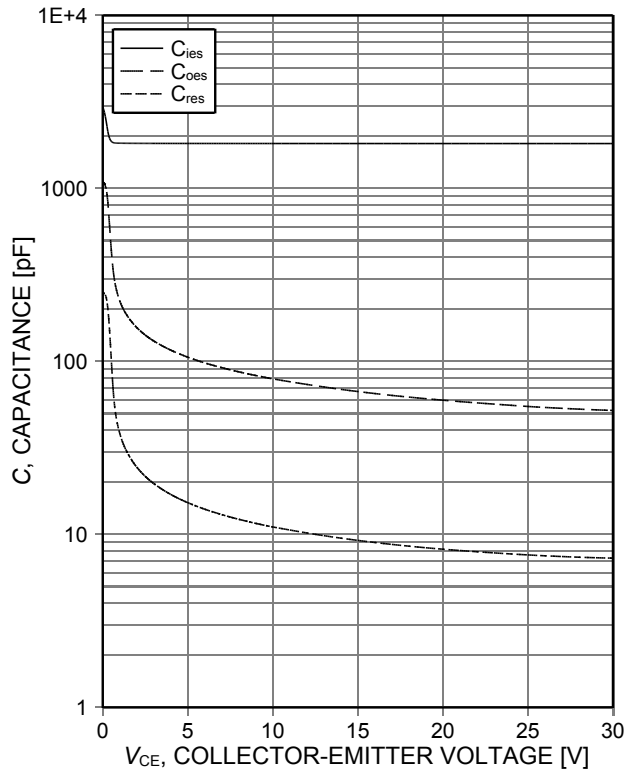


Figure 16. **Typical capacitance as a function of collector-emitter voltage** ($V_{GE}=0V$, $f=1MHz$)

High speed switching series 5th generation

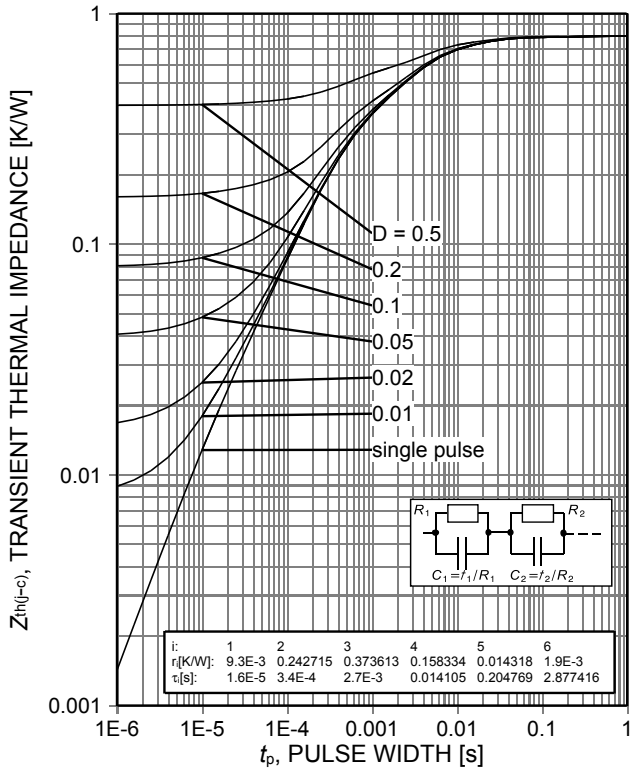


Figure 17. IGBT transient thermal impedance (D=t_p/T)

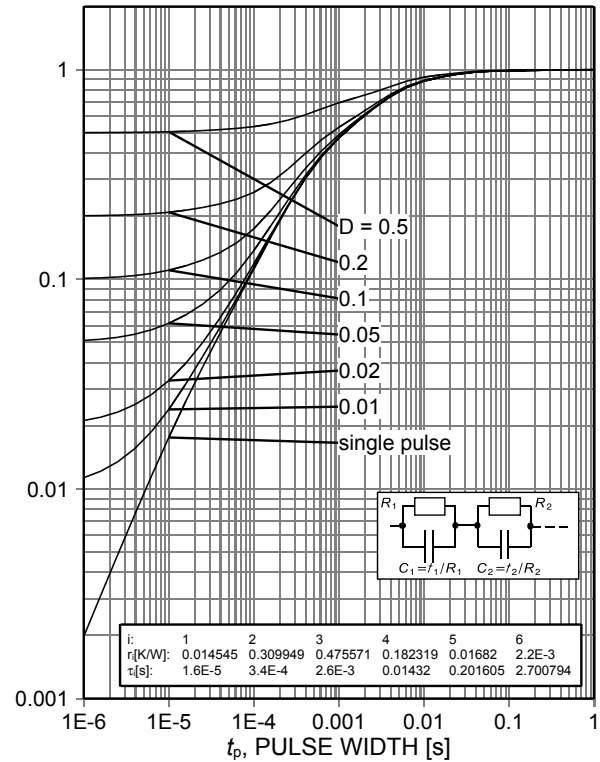


Figure 18. Diode transient thermal impedance as a function of pulse width (D=t_p/T)

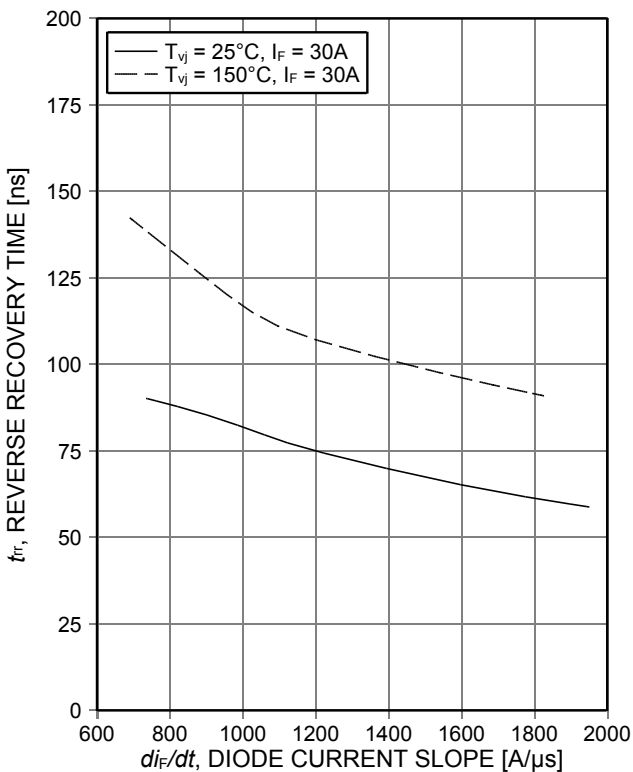


Figure 19. Typical reverse recovery time as a function of diode current slope (V_R=400V)

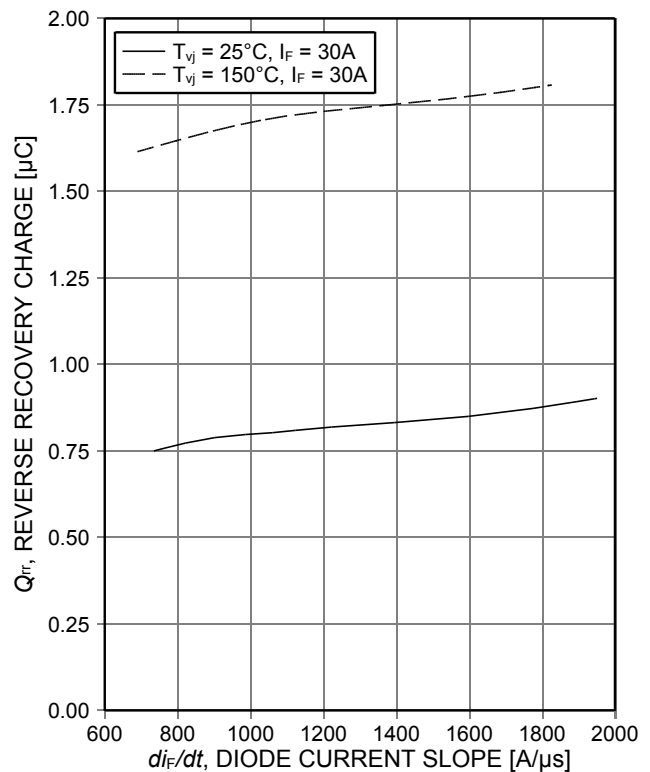


Figure 20. Typical reverse recovery charge as a function of diode current slope (V_R=400V)

High speed switching series 5th generation

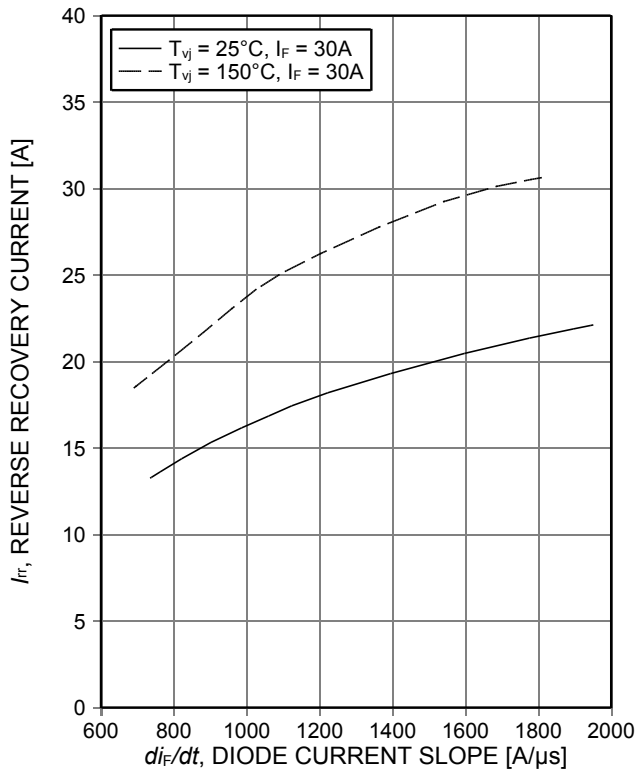


Figure 21. Typical reverse recovery current as a function of diode current slope ($V_R=400V$)

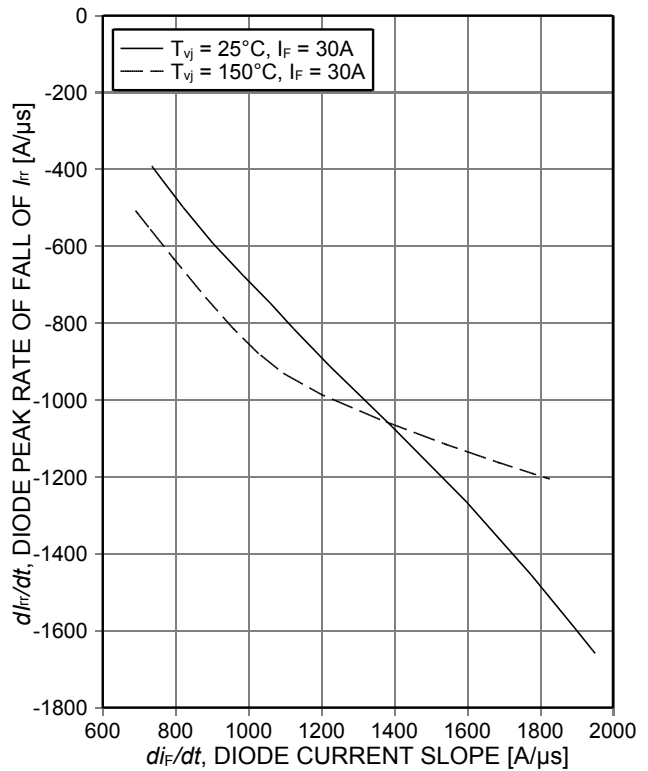


Figure 22. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope ($V_R=400V$)

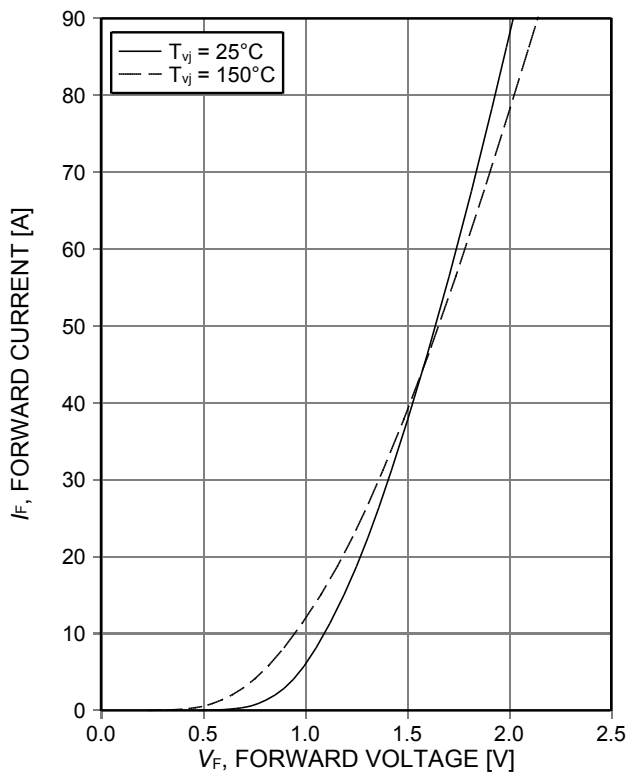


Figure 23. Typical diode forward current as a function of forward voltage

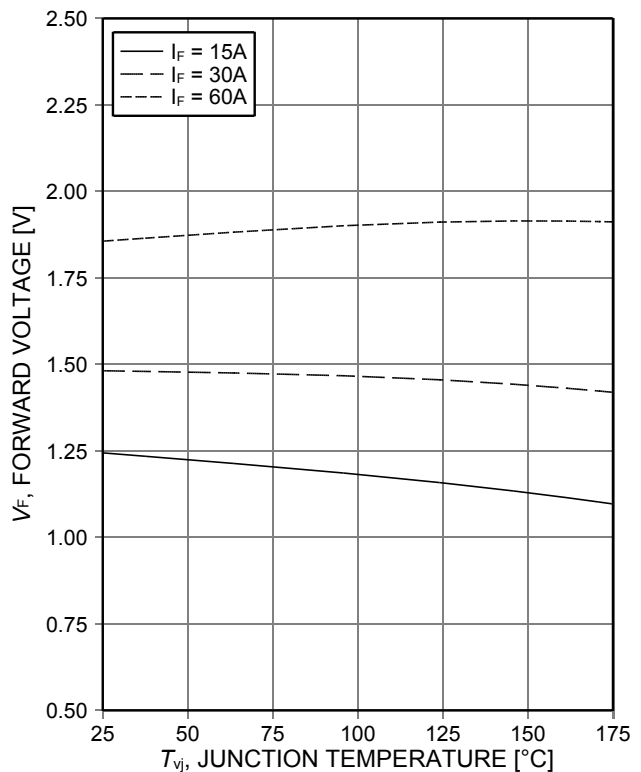
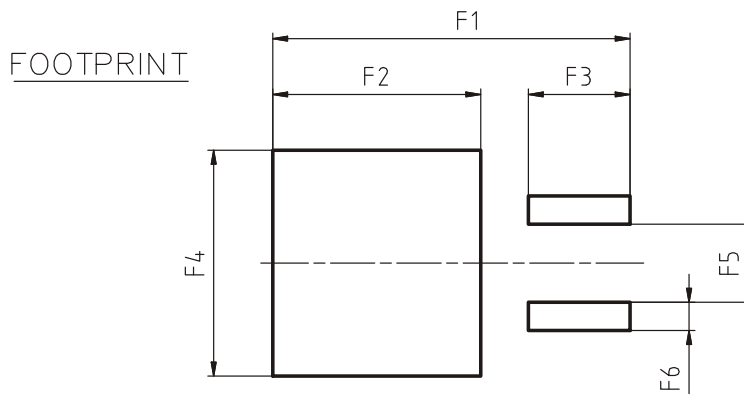
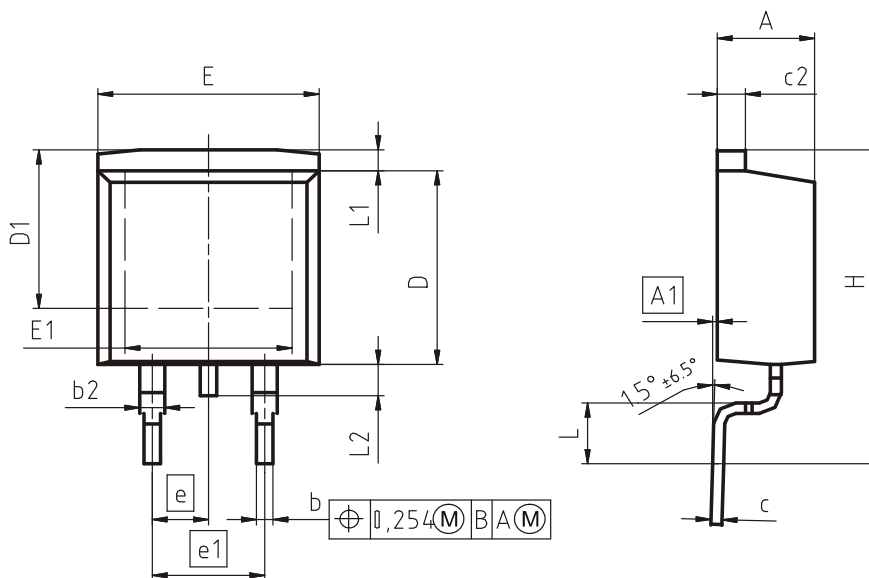


Figure 24. Typical diode forward voltage as a function of junction temperature

Package Drawing PG-TO263-3



| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|-------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.30 | 4.57 | 0.169 | 0.180 |
| A1 | 0.00 | 0.25 | 0.000 | 0.010 |
| b | 0.65 | 0.85 | 0.026 | 0.033 |
| b2 | 0.95 | 1.15 | 0.037 | 0.045 |
| c | 0.33 | 0.65 | 0.013 | 0.026 |
| c2 | 1.17 | 1.40 | 0.046 | 0.055 |
| D | 8.51 | 9.45 | 0.335 | 0.372 |
| D1 | 7.10 | 7.90 | 0.280 | 0.311 |
| E | 9.80 | 10.31 | 0.386 | 0.406 |
| E1 | 6.50 | 8.60 | 0.256 | 0.339 |
| e | 2.54 | | 0.100 | |
| e1 | 5.08 | | 0.200 | |
| N | 2 | | 2 | |
| H | 14.61 | 15.88 | 0.575 | 0.625 |
| L | 2.29 | 3.00 | 0.090 | 0.118 |
| L1 | 0.70 | 1.60 | 0.028 | 0.063 |
| L2 | 1.00 | 1.78 | 0.039 | 0.070 |
| F1 | 16.05 | 16.25 | 0.632 | 0.640 |
| F2 | 9.30 | 9.50 | 0.366 | 0.374 |
| F3 | 4.50 | 4.70 | 0.177 | 0.185 |
| F4 | 10.70 | 10.90 | 0.421 | 0.429 |
| F5 | 3.65 | 3.85 | 0.144 | 0.152 |
| F6 | 1.25 | 1.45 | 0.049 | 0.057 |

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SCALE

7.5mm

EUROPEAN PROJECTION

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30-08-2007

REVISION
01

Testing Conditions



Figure A. Definition of switching times



Figure B. Definition of switching losses

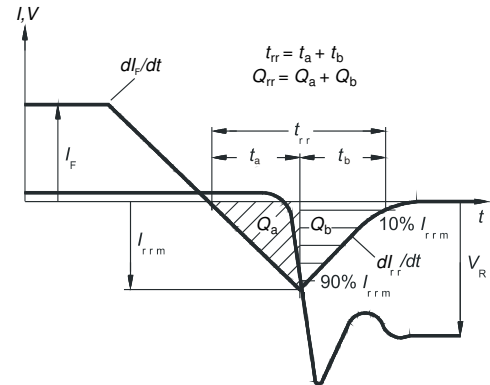


Figure C. Definition of diode switching characteristics



Figure D. Thermal equivalent circuit



Figure E. Dynamic test circuit
Parasitic inductance L_{σ} ,
parasitic capacitor C_{σ} ,
relief capacitor C_r ,
(only for ZVT switching)

High speed switching series 5th generation

Revision History

IKB30N65ES5

Revision: 2018-01-11, Rev. 2.1

Previous Revision

| Revision | Date | Subjects (major changes since last revision) |
|----------|------------|--|
| 2.1 | 2018-01-11 | Final data sheet |

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